VHF POWER MOSFET
N-Channel Enhancement Mode

DESCRIPTION:

The **VFT80-28** is Designed for General Purpose Class B Power Amplifier Applications up to 175 MHz.

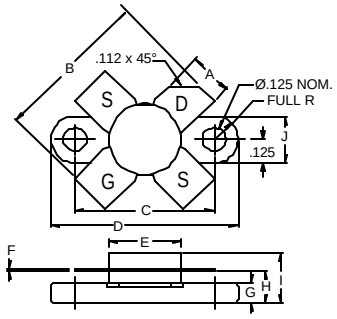
FEATURES:

- P_G = 10 dB Typical at 175 MHz
- **30:1 Load VSWR** Capability
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_D	7.0 A
$V_{(BR)DSS}$	60 V
V_{DGR}	60 V
V_{GS}	± 20 V
P_{DISS}	100 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.8 °C/W

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10704

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_D = 100 mA			60			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				5.0	mA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 20 V				1.0	µA
$V_{GS(th)}$	I_D = 25 mA	V_{DS} = 10 V		1.0		6.0	V
g_{fs}	I_D = 1 A	V_{DS} = 10 V		700			mS
C_{iss} C_{oss} C_{rss}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		52 87 8		pF
P_G	V_{DD} = 28 V	I_{DQ} = 25 mA	P_{out} = 45 W	12	15		dB
η_D			F = 175 MHz	50	60		%
ψ	V_{SWR} = 30:1 AT ALL PHASE ANGLES			NO DEGRADATION IN OUTPUT POWER			

Specifications are subject to change without notice.